Ordering number:EN4889

FX606

N-Channel Silicon MOSFET

Ultrahigh-Speed Switching Applications

Features

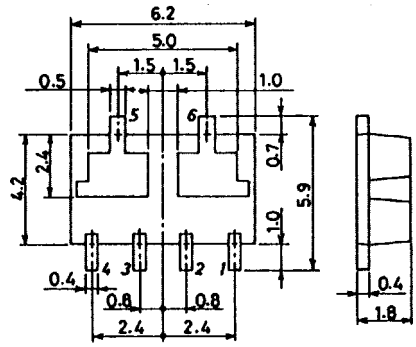
- Composite type composed of two low ON-resistance N-channel MOSFET chips for ultrahigh-speed switching and low-voltage drive.
- Facilitates high-density mounting.
- The FX606 is formed with two chips, each being equivalent to the 2SK1470, placed in one package.
- Matched pair characteristics.

Package Dimensions

unit:mm

2120

[FX606]

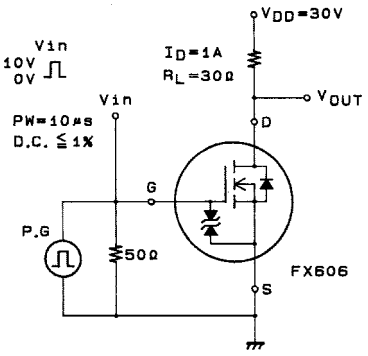


1:Gate1
2:Source1
3:Source2
4:Gate2
5:Drain2
6:Drain1

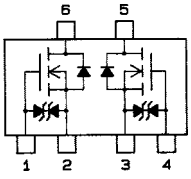
SANYO:XP6

(Bottom view)

Switching Time Test Circuit



Electrical Connection



1:Gate1
2:Source1
3:Source2
4:Gate2
5:Drain2
6:Drain1

(Top view)

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		60	V
Gate-to-Source Voltage	V_{GSS}		±15	V
Drain Current (DC)	I_D		2	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	8	A
Allowable Power Dissipation	P_D	Tc=25˚C, 1 unit	6	W
	P_D	Mounted on ceramic board (750mm²×0.8mm) 1 unit	1.5	W
Total Dissipation	P_T	Mounted on ceramic board (750mm²×0.8mm)	2	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

- Marking:606

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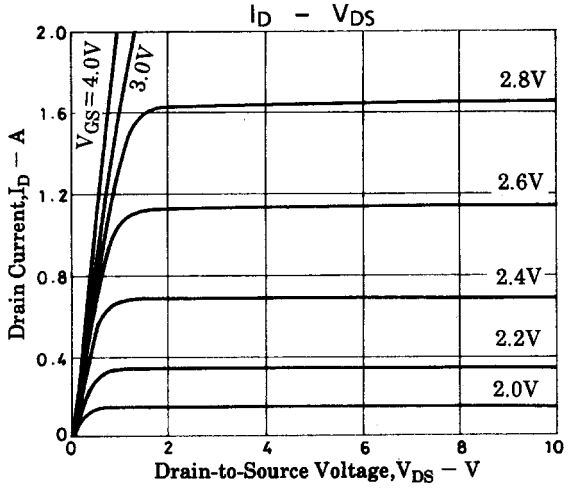
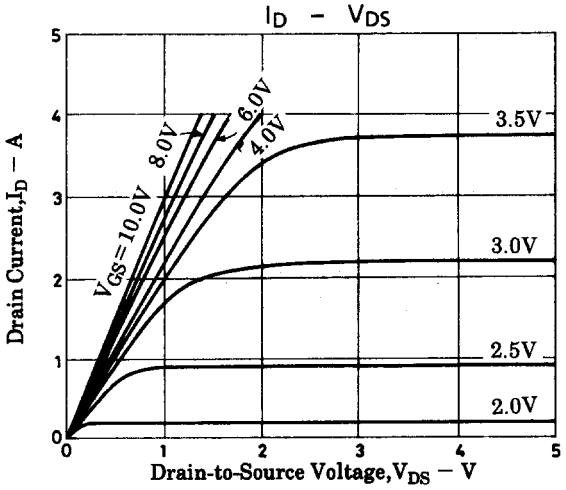
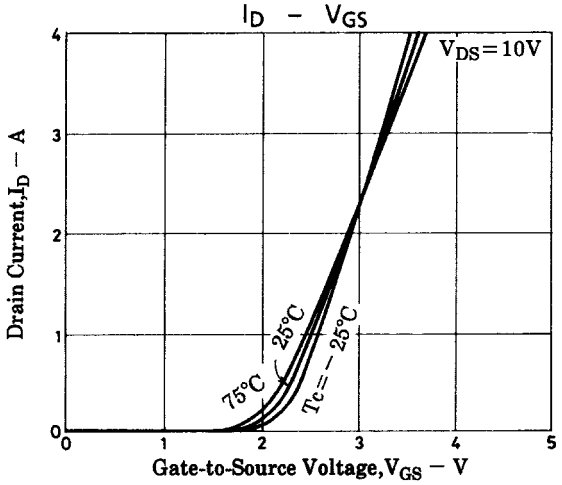
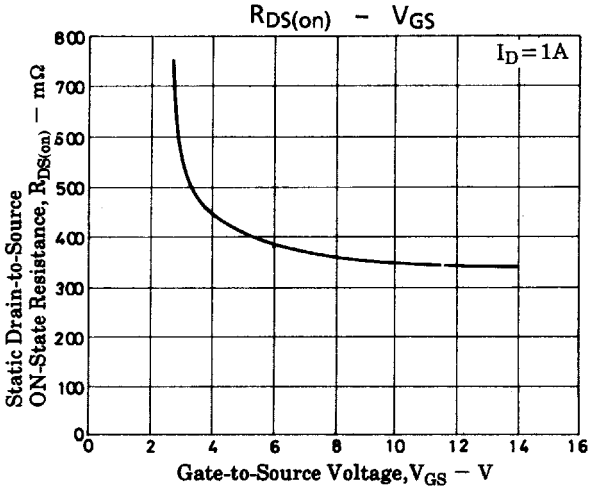
Electrical Characteristics at Ta = 25˚C

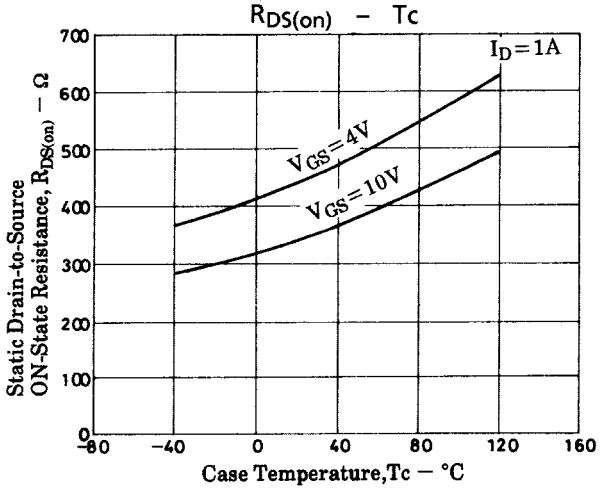
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	60			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±12, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, ID=1mA	1.0		2.0	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS}=10V, I_D=1A	1.2	2.0		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	I_D=1A, V_{GS}=10V		0.35	0.45	Ω
	$R_{DS(on)}$	I_D=1A, V_{GS}=4V		0.45	0.6	Ω
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		150		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		12		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		6		ns
Rise Time	t_r	See specified Test Circuit		10		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		60		ns
Fall Time	t_f	See specified Test Circuit		20		ns
Diode Forward Voltage	V_{SD}	I_S=1.2A, V_{GS}=0		1.0		V

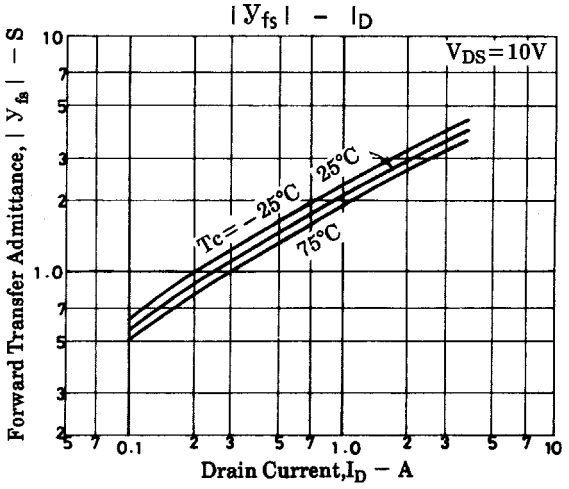

I_D – V_{DS}
Drain Current, I_D – A
Drain-to-Source Voltage, V_{DS} – V
V_{GS} = 4.0V
3.0V
2.8V
2.6V
2.4V
2.2V
2.0V

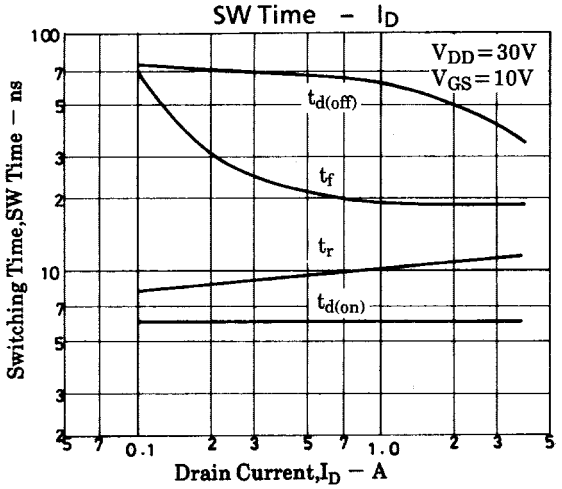

I_D – V_{DS}
Drain Current, I_D – A
Drain-to-Source Voltage, V_{DS} – V
V_{GS} = 10.0V
8.0V
6.0V
4.0V
3.5V
3.0V
2.5V
2.0V

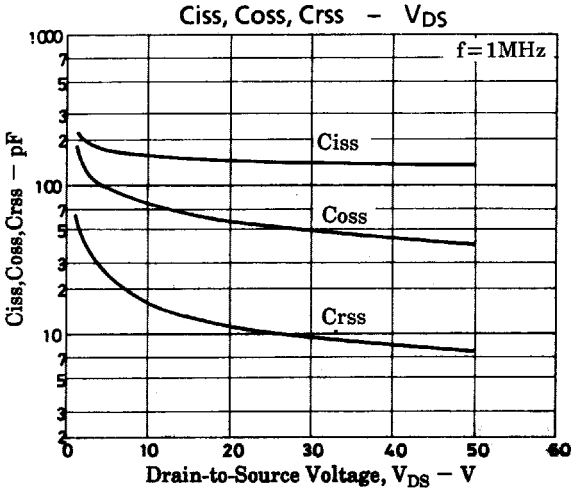

I_D – V_{GS}
Drain Current, I_D – A
Gate-to-Source Voltage, V_{GS} – V
V_{DS} = 10V
75°C
25°C
Tc = – 25°C


$R_{DS(on)}$ – V_{GS}
Static Drain-to-Source ON-State Resistance, $R_{DS(on)}$ – mΩ
Gate-to-Source Voltage, V_{GS} – V
I_D = 1A


$R_{DS(on)}$ – Tc
Static Drain-to-Source ON-State Resistance, $R_{DS(on)}$ – Ω
Case Temperature, Tc – °C
I_D = 1A
V_{GS} = 4V
V_{GS} = 10V


$|y_{fs}|$ – I_D
Forward Transfer Admittance, $|y_{fs}|$ – S
Drain Current, I_D – A
V_{DS} = 10V
Tc = – 25°C
25°C
75°C


SW Time – I_D
Switching Time, SW Time – ns
Drain Current, I_D – A
V_{DD} = 30V
V_{GS} = 10V
$t_{d(off)}$
t_f
t_r
$t_{d(on)}$


Ciss, Coss, Crss – V_{DS}
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, V_{DS} – V
f = 1MHz
Ciss
Coss
Crss